P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ)
–40	0.054 at V_{GS} = –10 V	–4.5	9
	0.072 at V_{GS} = –4.5 V	–3.9	

FEATURES

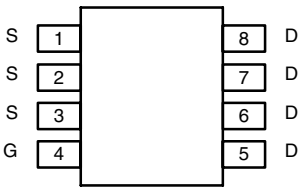
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- UIS Tested

APPLICATIONS

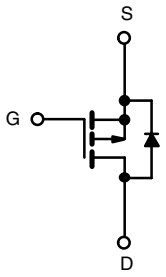
- CCFL Inverter

Pb-free
RoHS COMPLIANT

SO-8



Top View



P-Channel MOSFET

Ordering Information: Si4447DY–T1–E3 (Lead (Pb)–free)

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	–40		V
Gate-Source Voltage		V_{GS}	±16		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	–4.5	–3.3	A
	T_A = 70 °C		–3.6	–2.7	
Pulsed Drain Current		I_{DM}	30		
Continuous Source Current (Diode Conduction)[a]		I_S	–1.7	–0.9	
Avalanche Current	L = 0.1 mH	I_{AS}	16		
Single Pulse Avalanche Energy		E_{AS}	13		mJ
Maximum Power Dissipatio[a]	T_A = 25 °C	P_D	2	1.1	W
	T_A = 70 °C		1.3	0.7	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typ	Max	Unit
Maximum Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	50	62.5	°C/W
	Steady State		85	110	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	30	40	

Notes
a. Surface Mounted on 1" x 1" FR4 Board.

SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

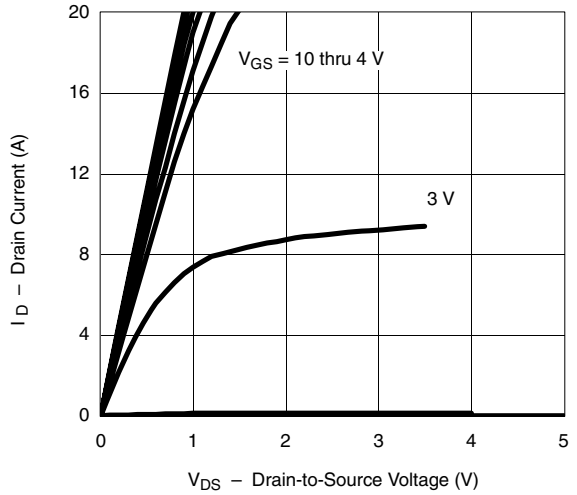
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = –250 µA	–0.8		–2.2	
V_{DS} Temperature Coefficient	$\Delta V_{DS/Tj}$	I_D = 250 µA		–40		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)/Tj}$			3.4		
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 16 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = –40 V, V_{GS} = 0 V			–1	µA
		V_{DS} = –40 V, V_{GS} = 0 V, T_J = 55 °C			–10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≤ –5 V, V_{GS} = –10 V	–20			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = –10 V, I_D = –4.5 A		0.045	0.054	Ω
		V_{GS} = –4.5 V, I_D = –3.9 A		0.059	0.072	
Forward Transconductance[a]	g_{fs}	V_{DS} = –15 V, I_D = –4.5 A		13		S
Diode Forward Voltage[a]	V_{SD}	I_S = –1.7 A, V_{GS} = 0 V		–0.79	–1.2	V
Dynamic[b]						
Input Capacitance	C_{iss}	P-Channel V_{DS} = –20 V, V_{GS} = 0 V, f = 1 MHz		805		pF
Output Capacitance	C_{oss}			120		
Reverse Transfer Capacitance	C_{rss}			85		
Total Gate Charge	Q_g	P-Channel V_{DS} = –20 V, V_{GS} = –4.5 V, I_D = –4.5 A		9	14	nC
Gate-Source Charge	Q_{gs}			2		
Gate-Drain Charge	Q_{gd}			3.6		
Gate Resistance	R_g	f = 1 MHz		11.5	18	Ω
Turn-On Delay Time	$t_{d(on)}$	P-Channel V_{DD} = –15 V, R_L = 15 Ω I_D ≅ –1 A, V_{GEN} = –10 V, R_g = 6 Ω		8	13	ns
Rise Time	t_r			12	18	
Turn-Off Delay Time	$t_{d(off)}$			74	110	
Fall Time	t_f			38	60	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 1.7 A, di/dt = 100 A/µs		27	45	ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F = 1.7 A, di/dt = 100 A/µs		17	26	nC

Notes
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

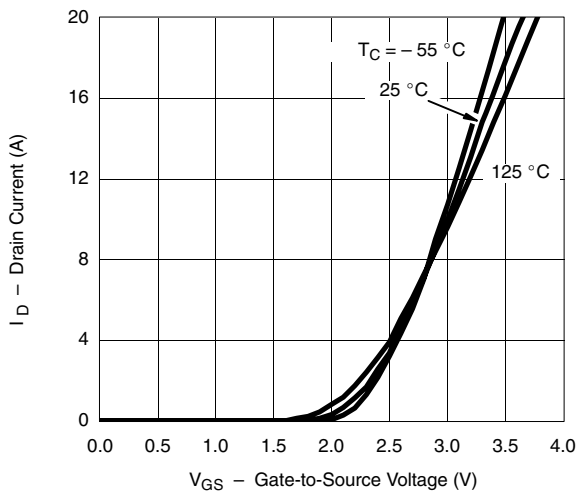
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

Output Characteristics

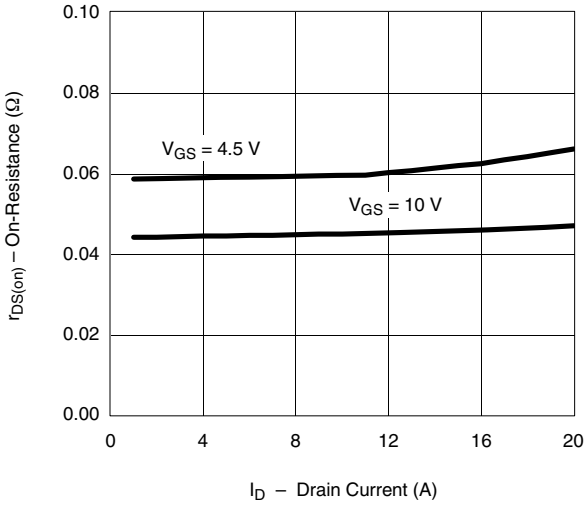


Transfer Characteristics

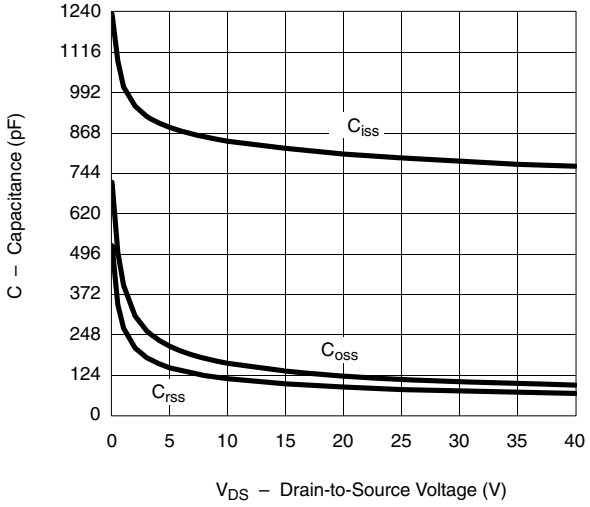


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

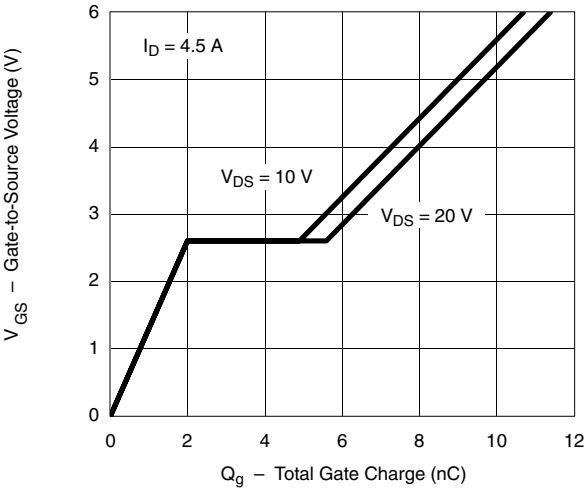
On-Resistance vs. Drain Current



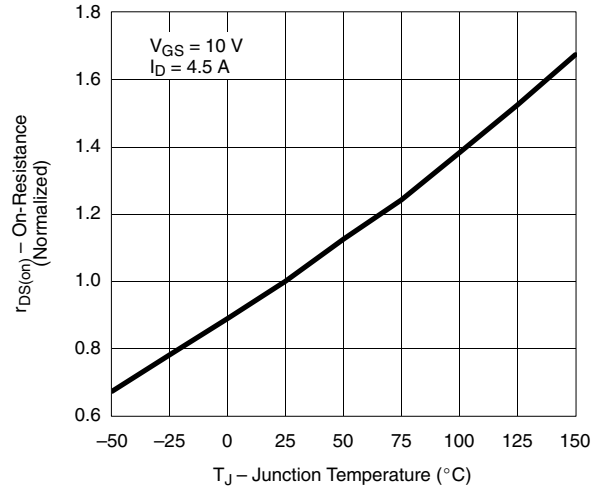
Capacitance



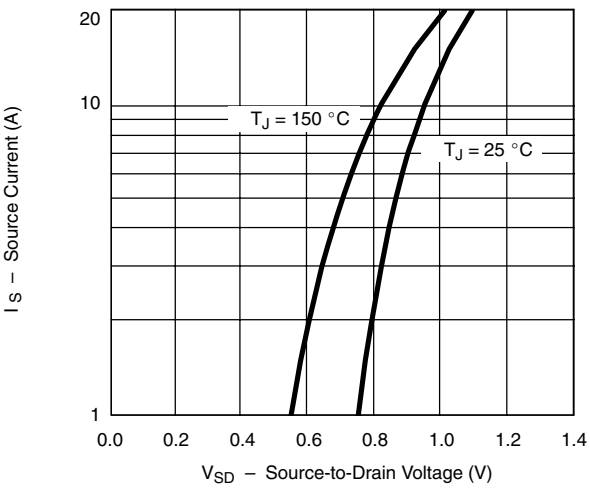
Gate Charge



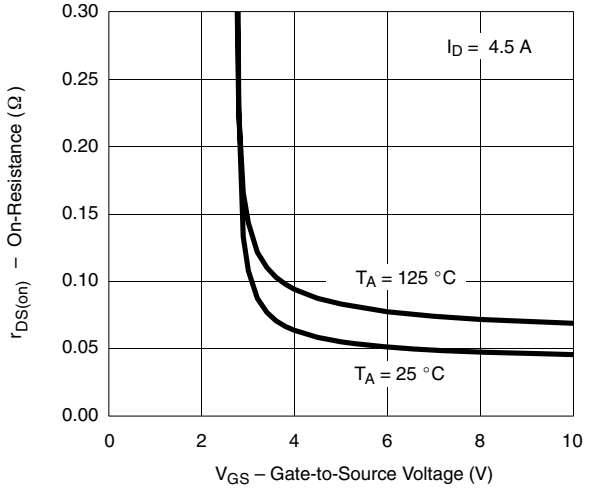
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

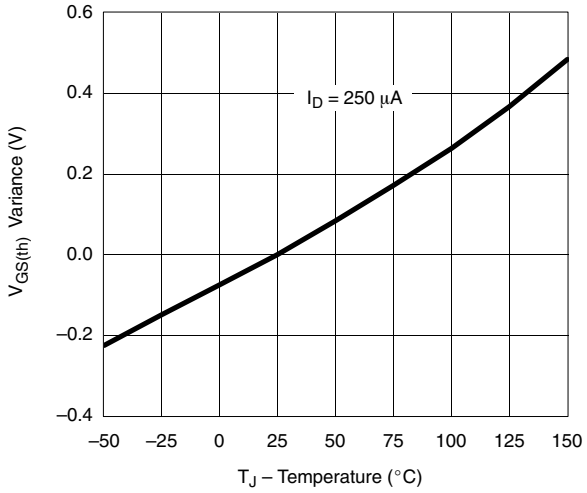


On-Resistance vs. Gate-to-Source Voltage

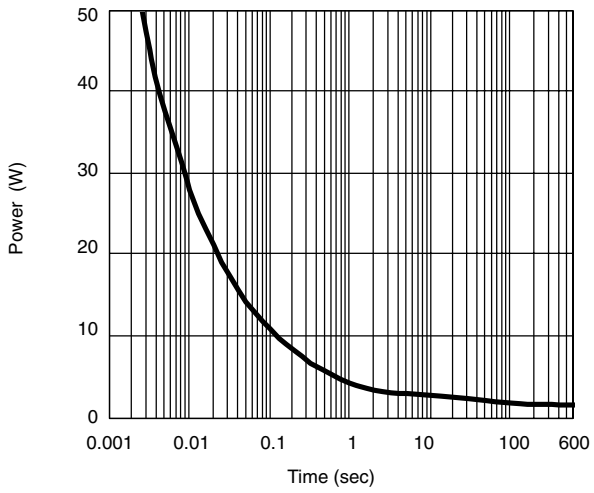


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

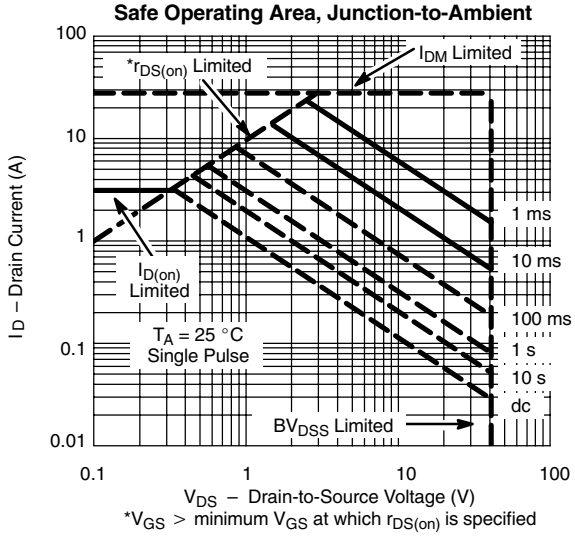
Threshold Voltage



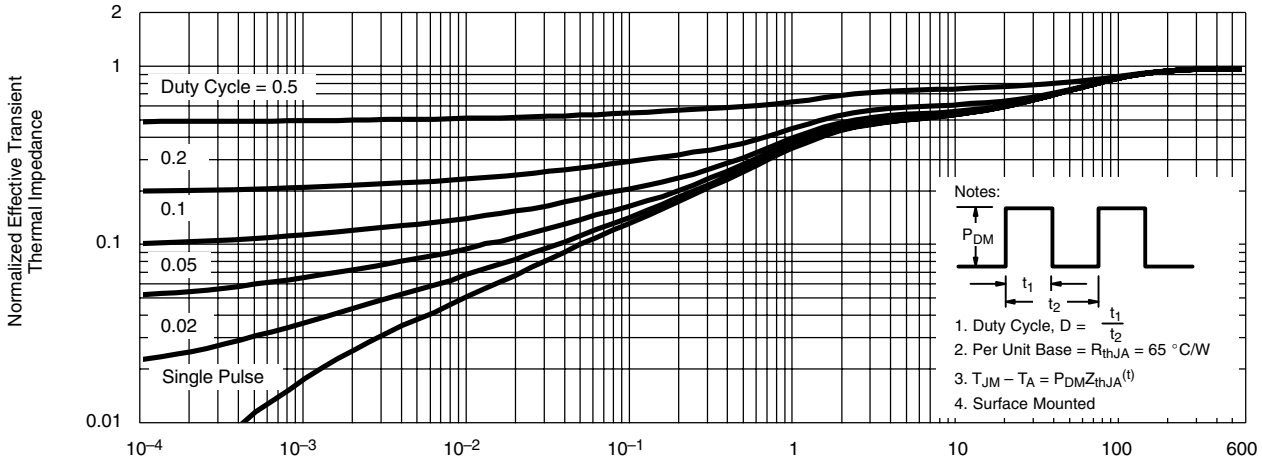
Single Pulse Power



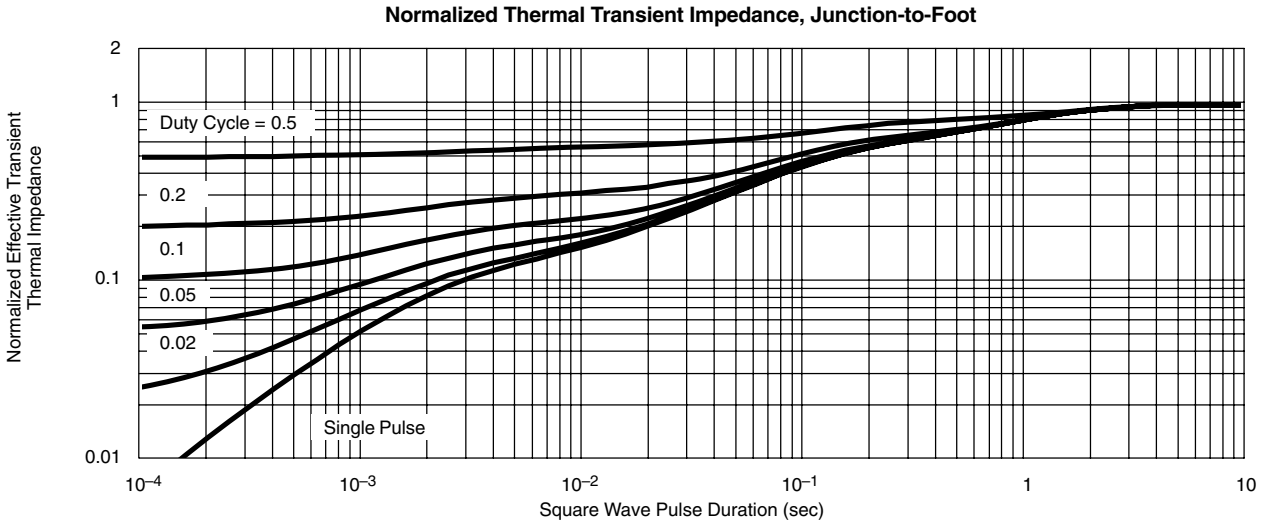
Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



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